

Citations for Target : **SiO₂**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Num
1960	Hines, R. L. 'Ranges of 7.5 to 52 keV H ⁺ , D ⁺ , He ⁺ , and Ne ⁺ Ions in Quartz.' <i>Phys. Rev.</i> , 120, 1626-30 (1960) <i>Comment</i> : R. 7.5-52 keV H ⁺ , D ⁺ , He ⁺ , Ne ⁺ -> SiO ₂ (Cryst.)	1960-Hine 0558
1966	Whitton, J. L. Matzke, Hj. 'The Effect of Crystallinity and Bombardment Dose on the Penetration of 40 keV Xenon Ions in Ionic Crystals and Ceramics' <i>Can. J. Phys.</i> , 44, 2905-14 (1966) <i>Comment</i> : R, dR. 40 keV Xe -> NaCl, KBr, MgO, SiO ₂ , UO ₂	1966-Whit 0276
1968	Tschalar, C. Bichsel, H. 'Mean Excitation Potential of Light Compounds' <i>Phys. Rev.</i> , 175, 476-8 (1968) <i>Comment</i> : R. 3-30 MeV H -> Si, Al, SiO ₂ , Al ₂ O ₃ , C ₃ H ₅ O ₂	1968-Tsch3 0904
1968	Volod'ko, V. G. Zorin, E. I. Pavlov, P. V. Tetel'baum, D. I. 'Distribution and Range of Boron and Phosphorus Ions used in Bombardment of SiO ₂ ' <i>Fiz. Tverd. Tela</i> , 10, 1048-52 (1968) [Engl. Trans. Sov. Phys. Solid State, 10, 828-31 (1968)] <i>Comment</i> : R, dR. 30-100 keV B, 50-150 keV P -> SiO ₂	1968-Volo 0349
1970	Bach, H. 'Zur Bestimmung der Reichweiten von Beschleunigten Ionen in Dunner Oxidschichten' <i>Z. Angew. Phys.</i> , 28, 239-44 (1970) <i>Comment</i> : R. 4.2-5.6 keV Ar -> SiO ₂ , TiO ₂	1970-Bach 0417
1971	Thompson, D. A. Mackintosh, W. D. 'Stopping Cross Sections for 0.3 - 1.7 MeV Helium Ions in Silicon and Silicion Dioxide.' <i>J. Appl. Phys.</i> , 42, 3969-76 (1971) <i>Comment</i> : S. 0.3-L.7 MeV He -> Si, SiO ₂	1971-Thom 0492
1971	Zhukova, G. A. Kesselman, V. S. Mordkovich, V. N. Zabolina, G. F. 'The Slowing Down of Low Energy Protons in SiO ₂ Films' <i>Zh. Eksp. Teor. Fiz.</i> , 59, 414-18 (1970). [Engl. Trans. Sov. Phys. JETP, 32, 226-28 (1971). <i>Comment</i> : R. 15-50 keV H -> SiO ₂	1971-Zhuk 0647
1972	Balzer, R. Sigrist, A. 'Disrimination of Heavy Ions by Track Detectors' <i>Helv. Phys. Acta</i> , 45, 921-2 (1972) <i>Comment</i> : S. Cl (8-30 MeV) -> Mica, Quartz, Spinel, Sapphire	1972-Balz 1286
1973	Bauer, L. -O. Macpherson, M. R. Robinson, A. T. Dill, H. G. 'Properties of Silicon Implanted with Boron Ions through Thermal Silicon Dioxide' <i>Solid-State Elec.</i> , 16, 289-300 (1973) <i>Comment</i> : R, dR. B (40-100 keV) -> Si Through SiO ₂	1973-Baue 1287

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1973	<p>Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. 'Range Distributions of Implanted Ions in SiO₂, Si₃N₄, and Al₂O₃' <i>Appl. Phys. Letters, 22, 490-92 (1973)</i> <i>Comment : R, dR. Zn, Ga, As, Se, Cd, Te (140-300 keV) -> SiO₂, Si₃N₄, Al₂O₃</i></p>	<table border="1"> <tr> <td>1973-Chu</td> </tr> <tr> <td>0013</td> </tr> </table>	1973-Chu	0013
1973-Chu				
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1973	<p>Combasson, J. L. Bernard, J. Guernet, G. 'Physical Profile Measurements in Insulating Layers using the Ion Analyzer' <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 285-94 (1973)</i> <i>Comment : R, dR. 60, 100 keV B -> SiO₂; 20, 40 keV B -> Si₃N₄; 60 keV B -> Si (Amorphous)</i></p>	<table border="1"> <tr> <td>1973-Comb</td> </tr> <tr> <td>0537</td> </tr> </table>	1973-Comb	0537
1973-Comb				
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1973	<p>Dunning, K. L. Hubsher, G. K. Comas, J. Lucks, W. H. Hughes, H. L. 'Depth Profiles of Aluminum and Sodium Near Surfaces: Nuclear Resonance Method' <i>Thin Solid Films, 19, 145-156 (1973)</i> <i>Comment : R, dR. 60 keV Al -> SiC, 20, 60 keV Na -> SiO₂</i></p>	<table border="1"> <tr> <td>1973-Dunn2</td> </tr> <tr> <td>0621</td> </tr> </table>	1973-Dunn2	0621
1973-Dunn2				
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1973	<p>Leich, D. A. Tombrello, T. A. 'A Technique for Measuring Hydrogen Concentration Versus Depth in Solid Samples' <i>Nucl. Inst. Methods, 108, 67-71 (1973)</i> <i>Comment : R, dR. 11.5 keV H -> SiO₂ (Cryst. And Amorph.), Feld Spar</i></p>	<table border="1"> <tr> <td>1973-Leic</td> </tr> <tr> <td>0800</td> </tr> </table>	1973-Leic	0800
1973-Leic				
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1973	<p>Presby, H. M. Brown, W. L. 'Refractive Index Variations in Proton Bombarded Fused Silica' <i>Appl. Phys. Letters, 24, 511-514 (1974)</i> <i>Comment : R. H (1.8 MeV) -> SiO₂ One of the earliest refractive index papers.</i></p>	<table border="1"> <tr> <td>1973-Pres</td> </tr> <tr> <td>2139</td> </tr> </table>	1973-Pres	2139
1973-Pres				
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1973	<p>Zohta, Y. 'Rapid Determination of Semiconductor Doping Profiles in Mos Structure' <i>Solid-State Elec., 16, 124-126 (1973)</i> <i>Comment : R. 40 keV B -> SiO₂, Si</i></p>	<table border="1"> <tr> <td>1973-Zoht</td> </tr> <tr> <td>0989</td> </tr> </table>	1973-Zoht	0989
1973-Zoht				
0989				
1974	<p>Bach, H. Kitzmann, I. Schroder, H. 'Sputtering Yields and Specific Energy Losses of Ar⁺ Ions with Energies from 5 to 30 keV at SiO₂' <i>Rad. Effects, 21, 31-36 (1974)</i> <i>Comment : S. 5-30 keV Ar -> SiO₂</i></p>	<table border="1"> <tr> <td>1974-Bach2</td> </tr> <tr> <td>0610</td> </tr> </table>	1974-Bach2	0610
1974-Bach2				
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1974	<p>Darwish, M. Y. Luginbuhl, H. W. 'Carrier Mobility Profiles for Low-Dose Boron-Implanted Layers' <i>Appl. Phys. Letters, 25, 390-391 (1974)</i> <i>Comment : R. 150 keV B -> SiO₂</i></p>	<table border="1"> <tr> <td>1974-Darw</td> </tr> <tr> <td>0984</td> </tr> </table>	1974-Darw	0984
1974-Darw				
0984				
1974	<p>EerNisse, E. P. 'Compaction of Ion Implanted Fused Silica' <i>J. Appl. Phys., 45, 167-174 (1974)</i> <i>Comment : R. H, He, O, Ne, Ar (150-300 keV) -> SiO₂ One of the earliest SiO₂ compaction studies.</i></p>	<table border="1"> <tr> <td>1974-EerN</td> </tr> <tr> <td>2138</td> </tr> </table>	1974-EerN	2138
1974-EerN				
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1974	Feng, J. S. -Y. Chu, W. K. Nicolet, M. -A. 'Stopping-Cross-Section Additivity for 1-2-MeV 4He+ in Solid Oxides' <i>Phys. Rev. B, 10, 3781-88 (1974)</i> <i>Comment : S. 1-2 MeV He -> MgO, Al₂O₃, SiO₂, He-Fe₂O₃, Fe₃O₄</i>	1974-Feng 0823
1975	Barcz, A. Turosz, A. Wielunski, L. Rosinski, W. Wojtowicz-Natanson, B. 'Depth Distribution of Silver Ions Implanted in Si and SiO₂' <i>Rad. Effects, 25, 91-96 (1975)</i> <i>Comment : R, dR. 20-140 keV 107Ag -> Si, SiO₂</i>	1975-Barc 0718
1975	Schimko, R. Richter, C. E. Rogge, K. Schwartz, G. Trapp, M. 'Implanted Arsenic and Boron Concentration Profiles in SiO₂ Layers' <i>Phys. Stat. Sol. A, 28, 87-93 (1975)</i> <i>Comment : R, dR. 40-300 keV 11B, 40-150 keV 75As, -> SiO₂</i>	1975-Schi 0518
1975	Wittmaack, K. Schulz, F. Hietel, B. 'Range Distributions of Boron in Silicon Dioxide and the Underlying Substrate' <i>Ion Implantation in Semiconductors, Namba (ed.), Plenum, N. Y. 193-200 (1975)</i> <i>Comment : R, dR. 5-150 keV 11B -> SiO₂</i>	1975-Witt 0747
1975	Ziegler, J. F. Chu, W. K. Feng, J. S. 'Empirical Corrections to the Energy Loss of 4He Ions in Oxides' <i>Appl. Phys. Letters, 27, 387-90 (1975)</i> <i>Comment : S. 2 MeV He -> Fe₂O₃, Fe₃O₄, MgO, Al₂O₃, SiO₂, Si₃N₄ All Rel. To Metal</i>	1975-Zieg 0880
1976	Abele, H. K. Glassel, P. Mair-Komor, P. Scheerer, H. J. Rosler, H. 'A Method for Measuring the Uniformity of Thin Targets by Means of an Alpha Source and a Q3D Spectrograph' <i>Nucl. Inst. Methods, 137, 157-67 (1976)</i> <i>Comment : dS. 8.78 MeV He -> C, Au, Ni, Al, SiO₂, Ru</i>	1976-Abel 0911
1976	Feuerstein, A. Grahmann, G. Kalbitzer, S. Oetzmann, H. 'Rutherford Backscattering Analysis with Very High Depth Resolution using an Electrostatic Analysing System' <i>Meyer, G. Linker and F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 471-81 (1976)</i> <i>Comment : dS. 100-200 keV P, D; 250 keV He -> Pt, Au, SiO₂</i>	1976-Feue 0844
1976	Natsuaki, N. Tamura, M. Tokuyama, T. 'Low Energy and High Dose Phosphorus Ion Implantation into Silicon through SiO₂ Film' <i>Jap. J. Appl. Phys., 15, 2427-2432 (1976)</i> <i>Comment : R. 3 keV P -> Si, SiO₂</i>	1976-Nats 1050
1976	Ryssel, H. Kranz, H. Biersack, J. Muller, K. Henkelmann, R. A. 'Boron Profiles and Diffusion Behavior in SiO₂-Si Structures' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 727-734 (1976)</i> <i>Comment : R. 30-150 keV B -> Si, SiO₂</i>	1976-Ryss 1015

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1976	Schertzer, B. M. U. Borgesen, P. Nicolet, M. -A. Mayer, J. W. 'Determination of Stopping Cross Sections by Rutherford Backscattering' <i>O. Meyer, G. Linker, F. Kappeler (Ed.): Ion Beam Surface Layer Analysis. Plenum, N. Y., 33-46 (1976)</i> <i>Comment : S. 0.2-2.0 MeV He -> Au, Pt, Ta₂O₅, SiO₂</i>	1976-Sche 0786
1976	Ziegler, J. F. Chu, W. K. Feng, J. S. 'Evidence of Solid State Effects in the Energy Loss of 4He Ions in Matter' <i>Meyer, G. Linker and F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 15-27 (1976)</i> <i>Comment : S. 2 MeV He -> Fe₂O₃, Fe₃O₄, MgO, Al₂O₃, SiO₂, Si₃N₄</i>	1976-Zieg2 0851
1977	Blamires, N. G. Smith, B. J. 'The Range of Doubly Charged Boron Ions' <i>J. Phys. D, 10, 799-804 (1977)</i> <i>Comment : R. 80, 360 keV B -> Si, SiO₂</i>	1977-Blam 1078
1977	Gartner, W. Schulz, M. 'Electronic Conduction Mechanisms of Cs- and B-Implanted SiO ₂ -Films' <i>Appl. Phys., 12, 137-148 (1977)</i> <i>Comment : R, dR. 60 keV Cs, 10 keV B -> SiO₂</i>	1977-Gart 1062
1977	Tsukamoto, K. Akasaka, Y. Horie, K. 'Range Distribution of Implanted Arsenic in Silicon Dioxide' <i>Jap. J. Appl. Phys., 16, 663-664 (1977)</i> <i>Comment : R, dR. 100-350 keV As -> SiO₂</i>	1977-Tsuk 1030
1978	Mittenbacher, J. Gartner, K. 'Proton Ranges in Silicon and in Si-SiO ₂ Double Layers' <i>Intl. Conf. Ion Beam Modification of Materials, Budapest -c (1978)</i> <i>Comment : R. 40-700 keV H -> Si, SiO₂</i>	1978-Mitt 1175
1979	Ishii, K. Blondiaux, G. Valladon, M. Debrun, D. L. 'The Study of Stopping Powers by the Method of the Average Stopping Power' <i>Nucl. Inst. Methods, 158, 199-203 (1979)</i> <i>Comment : S. T (3MeV) -> BeO, Al₂O₃, SiO₂, TiO₂, ZnO, Nb₂O₅, Ta₂O₅</i>	1979-Ishi 1539
1979	Muller, G. Trapp, M. Schimko, R. Richter, C. E. 'Measurement of Range Distributions of Zinc and Nitrogen Ions in Multiple-Layer Substrates with Secondary Ion Microprobe' <i>Phys. Stat. Sol. A, 51, 87-92 (1979)</i> <i>Comment : R, dR. 50-300 keV N, Zn -> SiO₂-GaAs(1-X)P(X), SiO₂-Si₃N₄</i>	1979-Mull 1237
1980	Muller, K. Henkelmann, R. Jahnel, F. Ryssel, H. Haberber, K. 'The Application of the (n,alpha)-Method of Boron Depth Profiling and Channeling - Blocking Measurement in Semiconductor Materials' <i>Preprint (1980) 6</i> <i>Comment : R, dR. 60-210 keV B -> Si, SiO₂</i>	1980-Mull 1363

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Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1982	Nakata, J. Kajiyama, K. 'Precise Profiles for Arsenic Implanted in Si and SiO ₂ over a Wide Implantation Energy Range (10 keV - 2.56 MeV)' <i>Jap. J. Appl. Phys.</i> , 21, 1363-1369 (1982) <i>Comment</i> : R. As (10 keV - 2.56 MeV) -> Si, SiO ₂	1982-Naka 2142
1983	Hautala, M. Paltemaa, R. Anttila, A. Luomajarvi, M. 'Ion Range Distributions in Oxides' <i>Nucl. Inst. Methods</i> , 209/210, 37-41 (1983) <i>Comment</i> : R. N(20-100 keV) -> SiO ₂ , MoO ₃ , Ta ₂ O ₅	1983-Haut 2020
1984	Rybka, V. Hnatowicz, V. Kvitek, J. Vacik, J. Schmidt, B. 'Determination of the Range Profiles of Boron Implanted into Si and SiO ₂ ' <i>Phys. Stat. Sol. A</i> , 83, 165-171 (1984) <i>Comment</i> : R, dR. B (30-200 keV) -> Si, SiO ₂	1984-Rybk 1446
1986	Santry, D. C. Werner, R. D. 'Energy Loss of He Ions in Al ₂ O ₃ and SiO ₂ ' <i>Nucl. Inst. Methods</i> , B14, 169-172 (1986) <i>Comment</i> : S. He(0.2-5.8 MeV) -> Al ₂ O ₃ , SiO ₂ , Al	1986-Sant 1194
1987	Grande, P. L. Fichtner, P. F. P. Behar, M. Livi, R. P. Zawislak, F. C. 'Projected Ranges and Range Straggling of Au and Bi Implanted into Carbon' <i>Nucl. Inst. Methods</i> , B19/20, 25-27 (1987) <i>Comment</i> : R, dR. Au, Bi (10-400 keV) -> C, SiO ₂	1987-Gran 1510
1987	Kido, Y. 'Energy Straggling for Fast Proton Beams Passing through Solid Materials' <i>Nucl. Inst. Methods</i> , B24/25, 347-352 (1987) <i>Comment</i> : H (300-1000 keV) -> C, Ti, TiC, Si, SiC, SiO ₂ , TiO ₂	1987-Kido 1664
1988	Fishbein, B. J. Plummer, J. D. 'Range Distribution of Implanted Cesium Ions in SiO ₂ Films' <i>J. Appl. Phys.</i> , 63, 5887-5889 (1988) <i>Comment</i> : R. Cs (50-145 keV) -> SiO ₂	1988-Fish 2016
1988	Grande, P. L. Fichtner, P. F. P. Behar, M. Zawislak, F. C. 'Range Profiles of Medium and Heavy Ions Implanted into SiO ₂ ' <i>Nucl. Inst. Methods</i> , B35, 17-20 (1988) <i>Comment</i> : R. As, Cs, Xe, Eu, Yb (10-200 keV) -> SiO ₂	1988-Gran 2022
1990	Bauer, P. 'Stopping Power of Light Ions near the Maximum' <i>Nucl. Inst. Methods</i> , B45, 673 (1990) <i>Comment</i> : dS. H, H- (30-700 keV) -> C, Al, Si, Ni, Cu, Ag, Au, SiO ₂ , HC ₂ , Al ₂ O ₃	1990-Baue 1608

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1992	Bauer, P. Rossler, W. Mertens, P. 'Stopping of Hydrogen Ions in Oxides - Influence of the Chemical Bond' <i>Nucl. Inst. Methods, B69, 46-52 (1992)</i> <i>Comment : S. H (300-350 keV) -> Al₂O₃, SiO₂</i>	1992-Baue2 1613
1992	Bichsel, H. Hiraoka, T. 'Energy Loss of 70 MeV Protons in Elements' <i>Nucl. Inst. Methods, B66, 345-351 (1992)</i> <i>Comment : S. H (70 MeV) -> C, H₂O, SiO₂, Al, Si, Ti, Cr, Fe, Co, Ni, Cu, Zn, Zr, Nb, Mo, Ag, Cd, In, Sn, Ta, W, Pb</i>	1992-Bich2 1624
1997	Bauer, P. Golser, R. Aumayr, F. Semrad, D. Arnau, A. 'Contribution of Valence Electrons to the Electronic Energy Loss of Hydrogen Ions in Oxides' <i>Nucl. Inst. Methods, B 125 102-105 (1997)</i> <i>Comment : S. H(10 - 1000 keV) -> H₂O, SiO₂, Al₂O₃, LiNbO₃</i>	1997-Baue 2366
1997	Eder, K. Semrad, D. Bauer, P. Golser, R. Echenique, P. M. 'Absence of a "Threshold Effect" in the Energy Loss of Slow Protons Traversing Large Band-Gap Insulators' <i>Phys. Rev. Lett., 79, 4112-4115 (1997)</i> <i>Comment : S. H (2 - 800 keV) -> Al₂O₃, SiO₂, LiF, Ne</i>	1997-Eder 2363
1998	Bauer, P. Golser, R. Semrad, D. Maier-Komor, P. Aumayr, F. 'Influence of the Chemical State on the Stopping of Protons and He-Ions in some Oxides' <i>Nucl. Inst. Methods, B 136-138, 103-108 (1998)</i> <i>Comment : S. H, He (0.03 - 1 MeV) -> Al₂O₃, SiO₂</i>	1998-Baue 2360